

Highly-efficient, regulated dual-output, ambient energy manager for AC or DC sources with optional primary battery

Features

Ultra-low-power start-up:

- Cold start from 380 mV input voltage and $3\,\mu W$ input power (typical)
- RF input power from -19 dBm up to 10 dBm (typical)

Ultra-low-power boost regulator:

- Open-circuit voltage sensing for MPPT every 0.33 s
- Configurable MPPT with 2-pin programming
- Selectable Voc ratios of 50, 65 or 80 %
- Input voltage operation range from 50 mV to 5 V
- MPPT voltage operation range from 50 mV to 5 V
- Constant impedance matching (ZMPPT)

Integrated 1.2/1.8 V LDO regulator:

- Up to 20 mA load current
- Power gated dynamically by external control
- Selectable output voltage

Integrated 1.8 V-4.1 V LDO regulator:

- Up to 80 mA load current with 300 mV drop-out
- Power gated dynamically by external control
- Selectable or adjustable output voltage

Flexible energy storage management:

- Selectable overcharge and overdischarge protection for any type of rechargeable battery or (super)capacitor
- Fast supercapacitor charging
- Warns the load when battery is running low
- Warns when output voltage regulators are available

Optional primary battery:

- Automatically switches to the primary battery when the secondary battery is exhausted

Integrated balun for dual-cell supercapacitor

Applications

- Piezo harvesting
- Home automation Transportation
- Micro turbine harvesting • RF harvesting
- Industrial monitoring
- Smart agriculture

Description

The AEM30940 is an integrated energy management circuit that extracts DC power from a piezo generator, a micro turbine generator or any high frequency RF input to simultaneously store energy in a rechargeable element and supply the system with two independent regulated voltages. The AEM30940 allows to extend battery lifetime and ultimately eliminates the primary energy storage element in a large range of wireless applications such as industrial monitoring, home automation, transportation and smart agriculture.

The AEM30940 harvests the available input current up to 110 mA. It integrates an ultra-low power boost converter to charge a storage element, such as a Li-ion battery, a thin film battery, a supercapacitor or a conventional capacitor. The boost converter operates with input voltages in a range from 50 mV to 5 V. With its unique cold-start circuit, it can start operating with empty storage elements at an input voltage as low as 380 mVand an input power of just $3\,\mu\text{W}.$

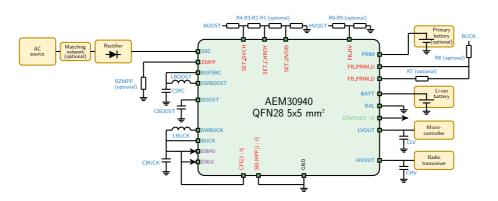
The low-voltage supply typically drives a microcontroller at 1.2 V or 1.8 V. The high-voltage supply typically drives a radio transceiver at a configurable voltage between 1.8 V and 4.1 V. Both are driven by highly-efficient LDO (Low Drop-Out) regulators for low noise and high stability.

Configuration pins determine various operating modes by setting predefined conditions for the energy storage element (overcharge or overdischarge voltages), and by selecting the voltage of the high-voltage supply and the low-voltage supply. Moreover, special modes can be obtained at the expense of a few configuration resistors.

The chip integrates all the active elements for powering a typical wireless sensor. Five capacitors and two inductors are required, available in the small 0402 and 0603 size, respectively. With only seven external components, integration is maximum, footprint and BOM are minimum, optimizing the timeto-market and the costs of WSN designs.

Device information

Part number	Package	Body size
10AEM30940C0000	QFN 28-pin	5 mm × 5 mm





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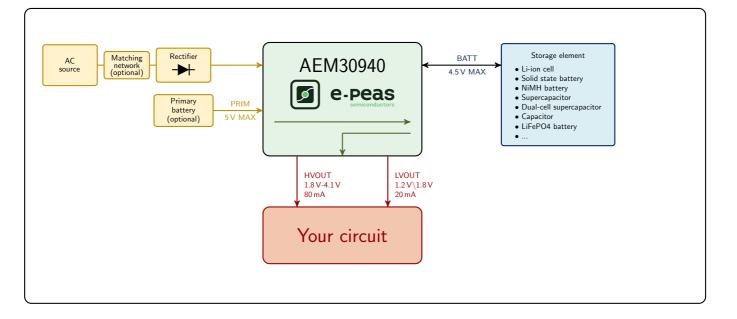


Figure 1: Simplified schematic view

1 Introduction

The AEM30940 is a full-featured energy efficient power management circuit able to charge a storage element (battery or supercapacitor, connected to BATT) from an energy source (connected to SRC) as well as to supply loads at different operating voltages through two power supplying LDO regulators (LVOUT and HVOUT).

The heart of the AEM30940 is a cascade of two regulated switching converters, namely the boost converter and the buck converter with high-power conversion efficiencies (See Page 18).

At first start-up, as soon as a required cold-start voltage of 380 mV and a scant amount of power of just $3\,\mu W$ available from the harvested energy source, the AEM coldstarts. After the cold start, the AEM can extract the power available from the source as long as the input voltage is comprised between 50 mV and 5 V.

Through three configuration pins (CFG[2:0]), the user can select a specific operating mode from a range of seven modes that cover most application requirements without any dedicated external component. Those operating modes define the LDO output voltages and the protection levels of the storage element. Note that a custom mode allows the user to define his own storage element protection levels and the output voltage of the high-voltage LDO (See Page 11). The Maximum Power Point (MPP) ratio can be configured using two configuration pins (SELMPP[1:0]) (See Page 12).

Two logic control pins are provided (ENLV and ENHV) to dynamically activate or deactivate the LDO regulators that supply the low- and high-voltage load, respectively. The status pin STATUS[0] alerts the user that the LDOs are operational and can be enabled. This signal can also be used to enable an optional external regulator.

If the battery voltage gets depleted, the LDOs are power gated and the controller is no longer supplied by the storage element to protect it from further discharge. Around 600 ms before the shutdown of the AEM, the status pin STATUS[1] alerts the user for a clean shutdown of the system.

However, if the storage element gets depleted and an optional primary battery is connected on PRIM, the chip automatically uses it as a source to recharge the storage element before switching back to the ambient source. This guarantees continuous operation even under the most adverse conditions (See Page 10). STATUS[1] is asserted when the primary battery is providing power.

The status of the MPP controller is reported with one dedicated status pin (STATUS[2]). The status pin is asserted when a MPP calculation is being performed.



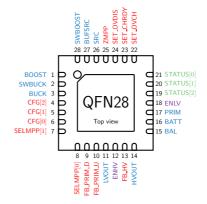


Figure 2: Pinout diagram QFN28

NAME	PIN NUMBER	FUNCTION		
Power pins				
BOOST	1	Output of the boost converter.		
SWBUCK	2	Switching node of the buck converter.		
BUCK	3	Output of the buck converter.		
LVOUT	11	Output of the low voltage LDO regulator.		
HVOUT	14	Output of the high voltage LDO regulator.		
BAL	15	Connection to mid-point of a dual-cell supercapacitor (optional). Must be connected to GND if not used.		
BATT	16	Connection to the energy storage element, battery or capacitor. Cannot be left floating.		
PRIM	17	Connection to the primary battery (optional). Must be connected to GND if not used.		
SRC	26	Connection to the harvested energy source.		
BUFSRC	27	Connection to an external capacitor buffering the boost converter inp	out.	
SWBOOST	28	Switching node of the boost converter.		
Configuration CFG[2]	pins 4			
CFG[1]	5	Used for the configuration of the threshold voltages for the		
CFG[0]	6	energy storage element and the output voltage of the LDOs.		
SELMPP[1]	7		See Page 11	
SELMPP	8	Used for the configuration of the MPP ratio.	Ũ	
FB_PRIM_D	9	Used for the configuration of the primary battery (optional).		
FB_PRIM_U	10	Must be connected to GND if not used.		
FB_HV	13	Used for the configuration of the high-voltage LDO in the custom mode (optional). Must be left floating if not used.		
SET_OVCH	22	Used for the configuration of the threshold voltages for		
SET_CHRDY	23	the energy storage element in the custom mode (optional).		
SET_OVDIS	24	Must be left floating if not used.		
ZMPPT	25	Used for the configuration of the ZMPPT (optional). Must be left floating if not used.		
Control pins	l			
ENHV	12	Enabling pin for the high-voltage LDO.	See Dage 0	
ENLV	18	Enabling pin for the low-voltage LDO.	See Page 9	
Status pins				
STATUS[2]	19	Logic output. Asserted when the AEM performs a MPP evaluation.	See	
STATUS[1]	20	Logic output. Asserted if the battery voltage falls below Vovdis or if the AEM is taking energy from the primary battery.	Pages 8-10	
STATUS[0]	21	Logic output. Asserted when the LDOs can be enabled.		
Other pins				
GND	Exposed Pad	Ground connection, should be solidly tied to the PCB ground plane.		

Table 1: Pins description

 \pm 1000 V

2 Absolute Maximum Ratings

Parameter	Rating
Vsrc	5.5 V
Operating junction temperature	-40 °C to $+125$ °C
Storage temperature	-65 °C to +150 °C

3 Thermal Resistance

Package	θ_{JA}	$ heta_{JC}$	Unit
QFN28	38.3	2.183	°C/W

Table 3: Thermal data

Table 2: Absolute maximum ratings

ESD CAUTION

V _{ESD}

ESD (ELECTROSTATIC DISCHARGE) SENSITIVE DEVICEThese devices have limited built-in ESD protection and damage may thus occur on devices subjected to
high-energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation
or loss of functionality.Human-body model according to Jedec JS001-2017± 500 V

4 Typical Electrical Characteristics at 25 °C

Charge device model according to Jedec JS002-2014

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Input voltag	e and input power					
Psrc _{CS}	Source power required for cold start.	During cold start	3			μW
Vsrc	Input voltage of the energy source.	During cold start	0.38		5	V
VSIC	input voltage of the energy source.	After cold start	0.05		5	v
DC-DC conv	verters					
Vboost	Output of the boost converter.	During normal operation	2.2		4.5	V
Vbuck	Output of the buck converter.	During normal operation	2	2.2	2.5	v
Storage elen	nent					
Vbatt	Voltage on the storage element.	Rechargeable battery	2.2		4.5	V
VDALL	Voltage on the storage element.	Capacitor	0		4.5	V
Tcrit	Time before shutdown after		400	600	800	ms
TCHL	STATUS[1] has been asserted.		400	000		-
Vprim	Voltage on the primary battery.		0.6		5	V
Vfb_prim_u	Feedback for the minimal voltage		0.15		1.1	V
vib_piiii_u	level on the primary battery.		0.15		1.1	v
	Maximum voltage accepted on the					
Vovch	storage element before disabling the	see Table 8	2.3		4.5	V
	boost converter.					
	Minimum voltage required on the		0.05			. /
Vchrdy	storage element before enabling the	see Table 8	2.25		4.45	V
	LDOs after a cold start.					
	Minimum voltage accepted on the		2.2			
Vovdis	storage element before switching to	see Table 8			4.4	V
	primary battery or entering into a shutdown.					
	LDO regulator					
Low-voltage	Output voltage of the low-voltage					
Vlv	LDO.	see Table 8	1.2		1.8	V
	Load current from the low-voltage					
llv	LDO.		0		20	mA
High-voltage	LDO regulator	l	I	L	l	
	Output voltage of the high-voltage					
Vhv	LDO.	see Table 8	1.8		Vbatt - 0.3	V
	Load current from the high-voltage					
lhv	LDO.		0		80	mA
Logic output	pins	<u> </u>		1	l	
	Logic output levels on the status	Logic high (VOH)	1.98	Vbatt		V
STATUS[2:0]	pins.	Logic low (VOL)	-0.1		0.1	V
J	1'	5 (-)		I	-	

Table 4: Electrical characteristics



5 Recommended Operation Conditions

Symbol	Parameter			Тур	Max	Unit	
External comp	External components						
CSRC	Capacitor decoupling the BUFSRC pi	n.	8	10	22	μF	
CBOOST	Capacitor of the boost converter.		10	22	25	μF	
LBOOST	Inductor of the boost converter.		4	10	25	μH	
CBUCK	Capacitor of the buck converter.		8	10	22	μF	
LBUCK	Inductor of the buck converter.		4	10	25	μH	
CLV	Capacitor decoupling the low-voltage	LDO regulator.	8	10	14	μF	
CHV	Capacitor decoupling the high-voltage	e LDO regulator.	8	10	14	μF	
CBATT	Optional - Capacitor on BATT if no is connected (see Page 12).	storage element	150			μF	
RT	Optional - Resistor for setting thresh battery in custom mode. Equal to $R1 + R2 + R3 + R4$ (see F	-	1	10	100	MΩ	
RV	Optional - Resistor for setting the output voltage of the high-voltage LDO in custom mode. Equal to $R5 + R6$ (see Page 11)		1	10	40	MΩ	
RZMPP	Optional - Resistor for the ZMPPT ((see Page 12).	configuration	10		1M	Ω	
RP	Optional - Resistor to be used with a primary battery. Equal to $R7 + R8$ (see Page 12).		100		500	kΩ	
Logic input pi	ns						
ENHV	Enabling pin for the high-voltage	Logic high (VOH)	1.75	Vbuck	Vbuck	V	
LINITY	LDO ¹ .	Logic low (VOL)	-0.01	0	0.01	v	
ENLV	Enabling pin for the low-voltage	Logic high (VOH)	1.75	Vbuck	Vboost	V	
	LDO^2 .	Logic low (VOL)	-0.01	0	0.01	v	
SELMPP[1:0]	Configuration pins for	Logic high (VOH)	Conne	ct to BU(CK		
	the MPP evaluation (see Table 9). Logic low (VOL)		Conne	ct to GNI	\supset		
CFG[2:0]	Configuration pins for	Logic high (VOH)	Connect to BUCK				
	the storage element (see Table 8).	Logic low (VOL)	Connect to GND				
STONBATT	Configuration pin to select the en-	Logic high (VOH)	Connect to BATT				
STORBATT	ergy source during the cold start.	Logic low (VOL)	Conne	ct to GNI)		

Table 5: Recommended operating conditions

Note 1: ENHV can be dynamically driven by a logic signal from the LV domain. For a static usage, connect to BUCK (High) or GND (Low).

Note 2: ENLV can be dynamically driven by a logic signal from the HV domain. For a static usage, connect to BUCK or BOOST (High) or GND (Low).



6 Functional Block Diagram

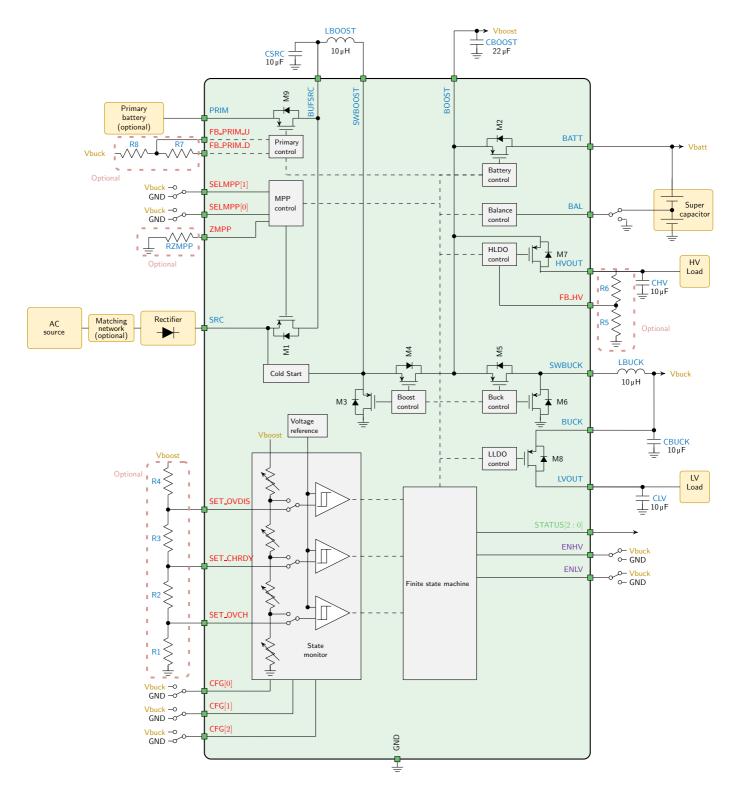


Figure 3: Functional block diagram



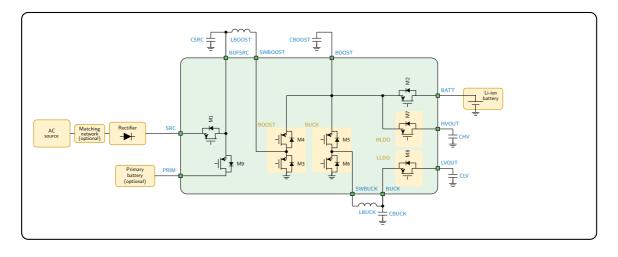


Figure 4: Simplified schematic view of the AEM30940

7 Theory of Operation

7.1 Deep sleep & Wake up modes

The DEEP SLEEP MODE is a state where all nodes are deeply discharged and there is no available energy to be harvested. As soon as the required cold-start voltage of 380 mV and a sparse amount of power of just $3\,\mu\text{W}$ becomes available on SRC , the WAKE UP MODE is activated. For RF source, the input power at the antenna is defined by the matching network and rectifier associater. See the Table 6 for e-peas results.Vboost and Vbuck rises up to a voltage of 2.2 V. Vboost then rises alone up to Vovch.

At that stage, both LDOs are internally deactivated. Therefore, ${\sf STATUS}[0]$ is equal to 0 as shown in Figure 9 and Figure 10.

When Vboost reaches Vovch, two scenarios are possible: in the first scenario, a super-capacitor or a capacitor having a voltage lower than Vchrdy is connected to the BATT node. In the second scenario, a charged battery is connected to the BATT node.

Frequency [MHz]	Pin [dBm]	Pin [µW]
863-868	-19	12.5
915-921	-19	12.5

Table 6: Minimum input power for the cold start (typical). Results obtained with the matching network and rectifier designed by e-peas

Supercapacitor as a storage element

If the storage element is a supercapacitor, the storage element may need to be charged from 0 V. The boost converter charges BATT from the input source and by modulating the conductance of M2. During the charge of the BATT node, both

LDOs are deactivated and STATUS[0] is de-asserted. When Vbatt reaches Vchrdy, the circuit enters NORMAL MODE, STATUS[0] is asserted and the LDOs can be activated by the user using the ENLV and ENHV control pins as shown in Figure 9.

Battery as a storage element

If the storage element is a battery, but its voltage is lower than Vchrdy, then the storage element first needs to be charged until it reaches Vchrdy. Once Vbatt exceeds Vchrdy, or if the battery was initially charged above Vchrdy, the circuit enters NORMAL MODE. STATUS[0] is asserted and the LDOs can be activated by the user thanks to ENLV and ENHV as shown in Figure 10.

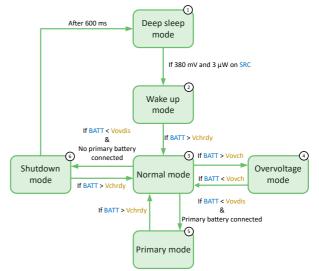


Figure 5: Diagram of the AEM30940 modes



7.2 Normal mode

Once the AEM enters NORMAL MODE, three scenarios are possible:

- There is enough power provided by the source to maintain Vbatt above Vovdis but Vbatt is below Vovch. In that case, the circuit remains NORMAL MODE.
- The source provides more power than the load consumes, and Vbatt increases above Vovch, the circuit enters into the OVERVOLTAGE MODE, as explained in the Overvoltage mode section.
- Due to a lack of power from the source, Vbatt falls below Vovdis. In this case, either the circuit enters SHUT-DOWN MODE as explained in Shutdown mode section or, if a charged primary battery is connected on PRIM, the circuit enters PRIMARY MODE as explained in the Primary mode section.

Matching network and rectifier

To connect AC sources to the AEM30940, an external rectifier is required as well as a matching network in the case of RF energy harvesting. The objective of the matching network is to modify the impedance relationship between the RF source and the rectifier in order to optimize the power transfer over a frequency band and an input power range. For RF applications, external high frequency rectifiers as well as matching networks are available ¹ for the following RF bands: 828 MHz, 915 MHz.

Boost

The boost (or step-up) converter raises the voltage available at BUFSRC to a level suitable for charging the storage element, in the range of 2.2 V to 4.5 V, according to the system configuration. This voltage (Vboost) is available at the BOOST pin. The switching transistors of the boost converter are M3 and M4, with the switching node available externally at SW-BOOST. The reactive power components of this converter are the external inductor and capacitor LBOOST and CBOOST. Periodically, the MPP control circuit disconnects the source from the BUFSRC pin with the transistor M1 in order to measure the open-circuit voltage of the harvester on SRC and define the optimal level of voltage. BUFSRC is decoupled by the capacitor CSRC, which smooths the voltage against the current pulses induced by the boost converter.

The storage element is connected to the BATT pin, at a voltage Vbatt. This node is linked to BOOST through the transistor M2. In NORMAL MODE, this transistor effectively shorts the battery to the BOOST node (Vbatt = Vboost). When energy harvesting is occurring, the boost converter delivers a current that is shared between the battery and the loads. M2 is opened to disconnect the storage element when Vbatt reaches Vovdis. However, in such a scenario, the AEM30940 offers the possibility of connecting a primary battery to recharge Vbatt up to the Vchrdy. The transistor M9 connects PRIM to BUF-

SRC and the transistor M1 is opened to disconnect the SRC input pin as explained in the Primary mode section and shown in Figure 13.

Buck

The buck (or step-down) converter lowers the voltage from Vboost to a constant Vbuck value of 2.2 V. This voltage is available at the BUCK pin. The switching transistors of the buck converter are M5 and M6, with the switching node available externally at SWBUCK. The reactive power components of the buck converter are the external inductor LBUCK and the capacitor CBUCK.

LDO outputs

Two LDOs are available to supply loads at different operating voltages:

Through M7, Vboost supplies the high-voltage LDO that powers its load through HVOUT. This regulator delivers a clean voltage (Vhv) with a maximum current of 80 mA on HVOUT. In the built-in configuration modes, an output voltage of 1.8 V, 2.5 V or 3.3 V can be selected. In the custom configuration mode, it is adjustable between 2.2 V and Vbatt-0.3 V.The high-voltage output can be dynamically enabled or disabled with the logic control pin ENHV. The output is decoupled by the external capacitor CHV.

Through M8, Vbuck supplies the low-voltage LDO that powers its load through LVOUT. This regulator delivers a clean voltage (VIv) of 1.8 V or 1.2 V with a maximum current of 20 mA on LVOUT. The low-voltage output can be dynamically enabled or disabled with the logic control pin ENLV. The output is decoupled by the external capacitor CLV.

Status pin STATUS[0] alerts the user when the LDOs can be enabled as explained in the Deep sleep & Wake up modes section and in the Shutdown mode section. The table below shows the four possible configurations:

ENLV	ENHV	LV output	HV output
1	1	Enabled	Enabled
1	0	Enabled	Disabled
0	1	Disabled	Enabled
0	0	Disabled	Disabled

Table 7: LDOs configurations

7.3 Overvoltage mode

When Vbatt reaches Vovch, the charge is complete and the internal logic maintains Vbatt around Vovch with a hysteresis of a few mV as shown in Figure 11 to prevent damage to the storage element and to the internal circuitry. In this configuration, the boost converter is periodically activated to maintain Vbatt and the LDOs are still available. Moreover, when the boost converter is not activated, the transistor M1 in Figure 4 is opened to prevent current from the source to the storage element when Vsrc is higher than Vovch.

¹Contact support@e-peas.com for additional information



7.4 Primary mode

When Vbatt drops below Vovdis, the circuit compares the voltage on PRIM with the voltage on FB_PRIM_U to determine whether a charged primary battery is connected on PRIM. The voltage on FB_PRIM_U is set thanks to two optional resistances as explained in the Primary battery configuration section. If the voltage on PRIM divided by 4 is higher than the voltage on FB_PRIM_U, the circuit considers the primary battery as available and the circuit enters PRIMARY MODE as shown in Figure 13.

In that mode, transistor M1 is opened and the primary battery is connected to BUFSRC through transistor M9 to become the source of energy for the AEM30940. The chip remains in this mode until Vbatt reaches Vchrdy. When Vbatt reaches Vchrdy, the circuit enters NORMAL MODE. As long as the chip is in PRIMARY MODE, STATUS[1] is asserted.

If no primary battery is used in the application, PRIM, FB_PRIM_U and FB_PRIM_D must be tied to GND.

7.5 Shutdown mode

When Vbatt drops below Vovdis and no power is available from a primary battery, the circuit enters SHUTDOWN MODE as shown in Figure 12 to prevent deep discharge potentially leading to damage to the storage element and instability of the LDOs. The circuit asserts STATUS[1] to warn the system that a shutdown will occur. Both LDO regulators remain enabled. If no primary battery is used, this allows the load, whether it is powered on LVOUT or HVOUT, to be interrupted by the lowto-high transition of STATUS[1], and to take all appropriate actions before power shutdown.

If energy at the input source is available and Vbatt recovers to Vchrdy within Tcrit (~ 600 ms), the AEM returns in NORMAL MODE. But if, after Tcrit, Vbatt does not reach Vchrdy, the circuit enters DEEP SLEEP MODE. The LDOs are deactivated and BATT is disconnected from BOOST to avoid damaging the battery due to the overdischarge. From now, the AEM will have to go through the wake-up procedure described in the Deep sleep & Wake up modes section.

7.6 Maximum power point tracking

During NORMAL MODE, SHUTDOWN MODE and a part of WAKE UP MODE, the boost converter is regulated thanks to

an internal MPPT (Maximum Power Point Tracking) module. Vmpp is the voltage level of the MPP, and depends on the input power available at the source. The MPPT module evaluates Vmpp as a given fraction of Voc, the open-circuit voltage of the source. By temporarily disconnecting the source from CSRC as shown in Figure 4 for 5.12 ms, the MPPT module receives from and maintains knowledge of Vmpp. This sampling occurs approximatively every 0.33 s .

With the exception of this sampling process, the voltage across the source, Vsrc, is continuously compared to Vmpp. When Vsrc exceeds Vmpp by a small hysteresis, the boost converter is switched on, extracting electrical charges from the source and lowering its voltage. When Vsrc falls below Vmpp by a small hysteresis, the boost converter is switched off, allowing the harvester to accumulate new electrical charges into CSRC, which restores its voltage. In this manner, the boost converter regulates its input voltage so that the electrical current (or flow of electrical charges) that enters the boost converter yields the best power transfer from the harvester under any ambient conditions. The AEM30940 supports any Vmpp level in the range from 0.05 V to 5 V. It offers a choice of four values for the Vmpp/Voc fraction or to match the input impedance of the BOOST converter with an impedance connected to the ZMPP terminal through configuration pins SELMPP[1:0] as shown in Table 9. The status of the MPPT controller is reported through one dedicated status pins (STATUS[2]). The status pin is asserted when a MPP calculation is being performed.

7.7 Balun for dual-cell supercapacitor

The balun circuit allows users to balance the internal voltage in a dual-cell supercapacitor in order to avoid damaging the super-capacitor because of excessive voltage on one cell. If BAL is connected to GND, the balun circuit is disabled. This configuration must be used if a battery, a capacitor or a single-cell supercapacitor is connected on BATT. If BAL is connected to the node between the cells of a supercapacitor, the balun circuit compensates for any mismatch of the two cells that could lead to over-charge of one of both cells. The balun circuit ensures that BAL remains close to Vbatt/2. This configuration must be used if a dual-cell supercapacitor is connected on BATT.



8 System Configuration

Configuration pins			Storage element threshold voltages			LDOs output voltages		Typical use
CFG[2]	CFG[1]	CFG[0]	Vovch	Vchrdy	Vovdis	Vhv	Vlv	
1	1	1	4.12 V	3.67 V	3.60 V	3.3 V	1.8 V	Li-ion battery
1	1	0	4.12 V	4.04 V	3.60 V	3.3 V	1.8 V	Solid state battery
1	0	1	4.12 V	3.67 V	3.01 V	2.5 V	1.8 V	Li-ion/NiMH battery
1	0	0	2.70 V	2.30 V	2.20 V	1.8 V	1.2 V	Single-cell supercapacitor
0	1	1	4.50 V	3.67 V	2.80 V	2.5 V	1.8 V	Dual-cell supercapacitor
0	1	0	4.50 V	3.92 V	3.60 V	3.3 V	1.8 V	Dual-cell supercapacitor
0	0	1	3.63 V	3.10 V	2.80 V	2.5 V	1.8 V	LiFePO4 battery
0	0	0	Custom mo	de - Program	mable throug	sh R1 to R6	1.8 V	

Table 8: Usage of CFG[2:0]

8.1 Battery and LDOs configuration

Through three configuration pins (CFG[2:0]), the user can set a particular operating mode from a range that covers most application requirements, without any dedicated external component as shown in Table 8. The three threshold levels are defined as:

- Vovch : Maximum voltage accepted on the storage element before disabling the boost converter,
- Vchrdy : Minimum voltage required on the storage element after a cold start before enabling the LDOs,
- Vovdis : Minimum voltage accepted on the storage element before considering the storage element as depleted.

See Theory of Operation section for more information about the purposes of these thresholds.

The two LDOs output voltages are called Vhv and Vlv for the high- and low-output voltages, respectively. In the built-in configuration mode, seven combinations of these voltage levels are hardwired and selectable through the CFG[2:0] configuration pins, covering most application cases. When a predefined configuration is selected, the resistor pins dedicated to a custom configuration should be left floating (SET_OVDIS, SET_CHRDY, SET_OVCH, FB_HV).

A custom mode allows the user to define the Vovch, Vchrdy, Vovdis and Vhv threshold voltages.

Custom mode

When CFG[2:0] are tied to GND, the custom mode is selected and all six configuration resistors shown in Figure 6, must be wired as follows:

Vovch, Vchrdy and, Vovdis are defined thanks to R1, R2, R3 and R4. If we define the total resistor (R1 + R2 + R3 + R4) as RT, R1, R2, R3 and R4 are calculated as:

- 1 $\text{M}\Omega \leq \text{RT} \leq$ 100 $\text{M}\Omega$
- R1=RT(1 V/Vovch)

- R2=RT(1 V/Vchrdy 1 V/Vovch)
- R3=RT(1 V/Vovdis 1 V/Vchrdy)
- R4=RT(1 1 V/Vovdis)

Vhv is defined thanks to R5 and R6. If we define the total resistor(R5 + R6) as RV, R5 and R6 are calculated as:

- 1 M $\Omega \leq \mathsf{RV} \leq$ 40 M Ω
- R5=RV(1 V/Vhv)
- R6=RV(1 1 V/Vhv)

The resistors should have high values to make the additional power consumption negligible. Moreover, the following constraints must be adhered to ensure the functionality of the chip:

- Vchrdy + 0.05 V \leq Vovch \leq 4.5 V
- Vovdis + 0.05 V \leq Vchrdy \leq Vovch 0.05 V
- 2.2 V \leq Vovdis
- Vhv \leq Vovdis 0.3 V

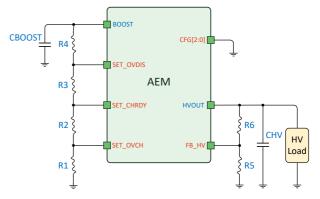


Figure 6: Custom configuration resistors



8.2 MPPT configuration

Two dedicated configuration pins, SELMPP[1:0], allow selecting the MPP tracking ratio based on the characteristic of the input power source.

SELMPP[1]	SELMPP[0]	Vmpp/Voc
0	0	50 %
0	1	65 %
1	0	80 %
1	1	ZMPP

Table 9: Usage of SELMPP[1:0]

8.3 Primary battery configuration

To use the primary battery, it is mandatory to determine Vprim_min, the voltage of the primary battery at which it has to be considered as empty. During the evaluation of Vprim_min, the circuit connects FB_PRIM_D to GND. The circuit uses a resistive divider between BUCK and FB_PRIM_D to define the voltage on FB_PRIM_U as Vprim_min divided by 4. When Vprim_min is not evaluated, FB_PRIM_D is left floating to avoid quiescent current on the resistive divider. If we define the total resistor (R7 + R8) as RP, R7 and R8 are calculated as:

- 100 k $\Omega \leq \mathsf{RP} \leq$ 500 k Ω
- R7= $\left(\frac{\text{Vprim}_{min}}{4} * \text{RP}\right)/2.2 \text{ V}$
- R8=RP-R7

Note that FB_PRIM_U and FB_PRIM_D must be tied to GND if no primary battery is used.

8.4 ZMPPT configuration

Instead of working at a ratio of the open-circuit voltage, the AEM30940 can regulate the input impedance of the BOOST converter so that it matches a constant impedance connected to the ZMPP pin (RZMPP). In this case, the AEM30940 regulates Vsrc at a voltage equals to the product of the ZMPP impedance and the current available at the SRC input.

• 10 $\Omega \leq \mathsf{RZMPP} \leq 1~\mathsf{M}\Omega$

8.5 No-battery configuration

If the harvested energy source is permanently available and covers the application purposes or if the application does not need to store energy when the harvested energy source is not available, the storage element may be replaced by an external capacitor CBATT of minimum 150 μ F.

8.6 Storage element information

The energy storage element of the AEM30940 can be a rechargeable battery, a supercapacitor or a large capacitor (minimum 150 μF). It should be chosen so that its voltage does not fall below Vovdis even during occasional peaks of the load current. If the internal resistance of the storage element cannot sustain this voltage limit, it is advisable to buffer the battery with a capacitor.

The BATT pin that connects the storage element must never be left floating. If the application expects a disconnection of the battery (e.g. because of a user removable connector), the PCB should include a capacitor of at least 150 μ F. The leakage current of the storage element should be small as leakage currents directly impact the quiescent current of the subsystem.

External inductors information

The AEM30940 operates with two standard miniature inductors of 10 μ H. LBOOST and LBUCK must respectively sustain a peak current of at least 250 mA and 50 mA and a switching frequency of at least 10 MHz. Low equivalent series resistance (ESR) favors the power conversion efficiency of the boost and buck converters.

External capacitors information

The AEM30940 operates with four identical standard miniature ceramic capacitors of 10 μF and one miniature ceramic capacitor of 22 μF . The leakage current of the capacitors should be small as leakage currents directly impact the quiescent current of the subsystem.

CSRC

This capacitor acts as an energy buffer at the input of the boost converter. It prevents large voltage fluctuations when the boost converter is switching. The recommended value is 10 μ F +/- 20 %.

CBUCK

This capacitor acts as an energy buffer for the buck converter. It also reduces the voltage ripple induced by the current pulses inherent to the switched mode of the converter. The recommended value is 10 μ F +/- 20 %.

CBOOST

This capacitor acts as an energy buffer for the boost converter. It also reduces the voltage ripple induced by the current pulses inherent to the switched mode of the converter. The recommended value is 22 μ F +/- 20 %.

$\mathsf{CHV} \text{ and } \mathsf{CLV}$

These capacitors ensure a high-efficiency load regulation of the high-voltage and low-voltage LDO regulators. Closed-loop stability requires the value to be in the range of 8 μF to 14 $\mu F.$





9 Typical Application Circuits

9.1 Example circuit 1

Power receiving

antenna

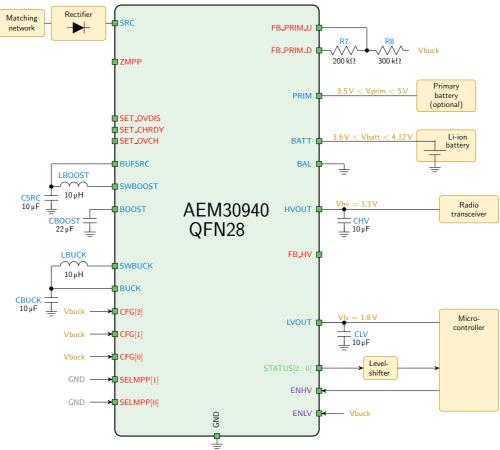


Figure 7: Typical application circuit 1

The energy source is a RF source, and the storage element is a standard Li-ion battery cell. The radio communication makes use of a transceiver that operates from a 3.3 V supply. A micro-controller supplied by a 1.8 V supply controls the application.

This circuit uses a pre-defined operating mode, typical of systems that use standard components for radio and energy storage.

The operating mode pins are connected to:

• CFG[2:0] = 111

Referring to Table 8, in this mode, the threshold voltages are:

- Vovch = 4.12 V
- Vchrdy = 3.67 V
- Vovdis = 3.60 V

Moreover, the LDOs output voltages are:

- Vhv = 3.3 V
- VIv = 1.8 V

A primary battery is also connected as a back-up solution. The minimal level allowed on this battery is set at 3.5 V. Following equations on Page 12:

- $RP = 0.5 M\Omega$
- R7 = $(\frac{3.5 \text{ V}}{4}$ *0.5 M Ω)/2.2 V = 200 k Ω
- R8 = 0.5 M Ω -200 k Ω = 300 k Ω

The MPP configuration pins SELMPP[1:0] are tied to GND (logic low), selecting an MPP ratio of 50 %.

The ENLV enable pin for the low-voltage LDO is tied to BUCK. The microcontroller will be enabled when Vbatt and Vboost exceed Vchrdy as the low-voltage regulator supplies it.

The application software can enable or disable the radio transceiver with a GPIO connected to $\mathsf{ENHV}.$



9.2 Example circuit 2

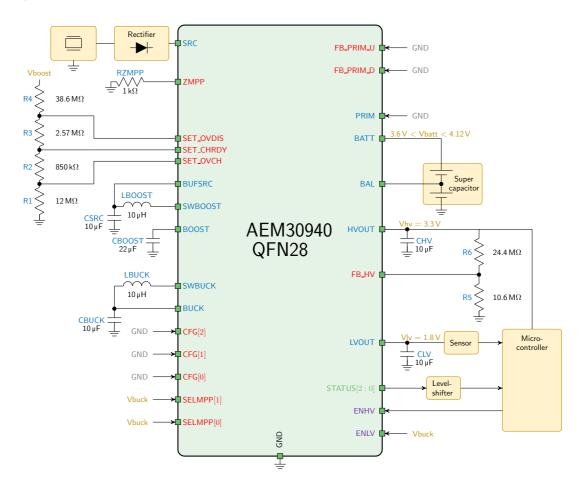


Figure 8: Typical application circuit 2

The energy source is a piezo source, and the storage element is a dual-cell supercapacitor. The supercapacitor can be completely depleted during the cold start.

Moreover, BAL is connected to the dual-cell supercapacitor to compensate for any mismatch between the two cells and in that way protect the supercapacitor.

A micro-controller pilots and collects information from a sensor. The operating mode pins are connected to:

• CFG[2:0]= 000

The user wants a custom configuration with Vovch, Vchrdy and Vovdis at 4.5 V, 4.2 V and 3.5 V, respectively. The user choose 54 M Ω for RT. Following the equation in page 11:

- R1=54 M $\Omega(\frac{1 \text{ V}}{4.5 \text{ V}})$ =12 M Ω
- R2=54 M $\Omega(\frac{1}{42})$ $\frac{1}{45}$ = 850 k Ω
- R3=54 M $\Omega(\frac{1 V}{3.5 V} \frac{1 V}{4.2 V})$ =2.57 M Ω

• R4=54 M
$$\Omega(1-\frac{1}{3.5} \frac{V}{V})$$
=38.6 M Ω

In the custom mode, the VIv equals 1.8 V and the application software can enable or disable the sensor with a GPIO connected to ENLV.

On Vhv, the user wants a 3.3 V voltage. As shown in page 11, the user chooses a resistor RV equal to 35 $M\Omega$

- R5=35 M $\Omega(\frac{1 \text{ V}}{3 3 \text{ V}})$ =10.6 M Ω
- R6=35 M Ω (1- $\frac{1}{3.3}$ V)=24.4 M Ω

The ENHV enable pin for the high-voltage LDO is tied to BUCK. The microcontroller is enabled when Vbatt and Vboost exceeds Vchrdy as the high-voltage regulator supplies it.

The MPP configuration pins SELMPP[1:0] are tied to BUCK (logic high), selecting the ZMPPT configuration to match a 1 K Ω impedance.

No primary battery is connected and the PRIM, FB_PRIM_U and FB_PRIM_D pins are tied to GND.





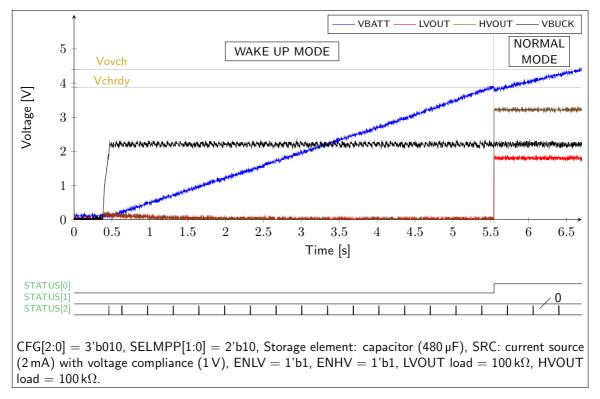


Figure 9: Cold start with a capacitor connected to BATT

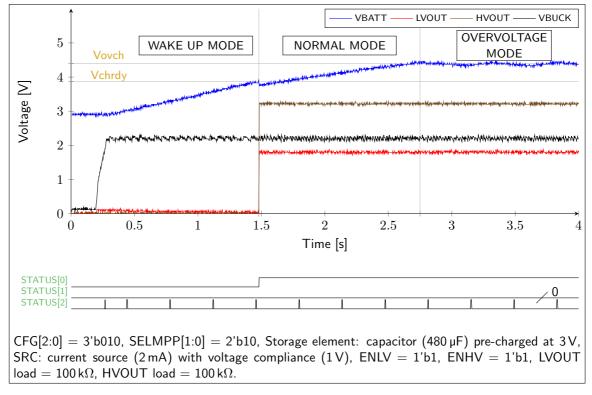


Figure 10: Cold start with a battery connected to BATT





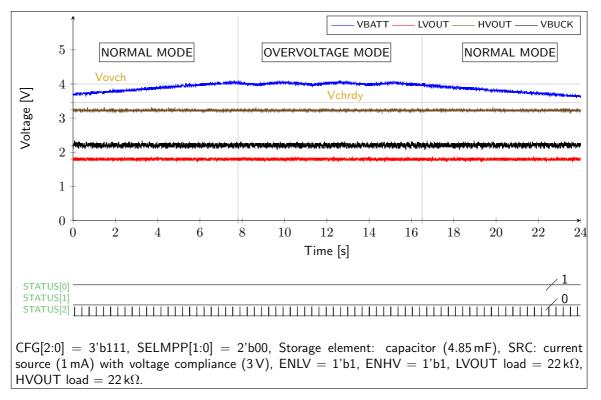


Figure 11: Overvoltage mode

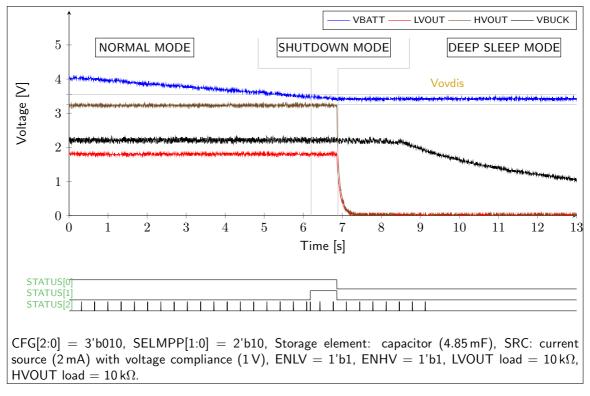


Figure 12: Shutdown mode (without primary battery)





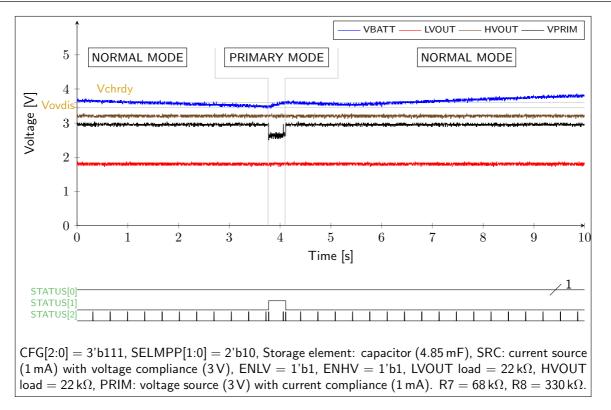


Figure 13: Switch to primary battery if the battery is overdischarged



10 Performance Data

10.1 BOOST conversion efficiency

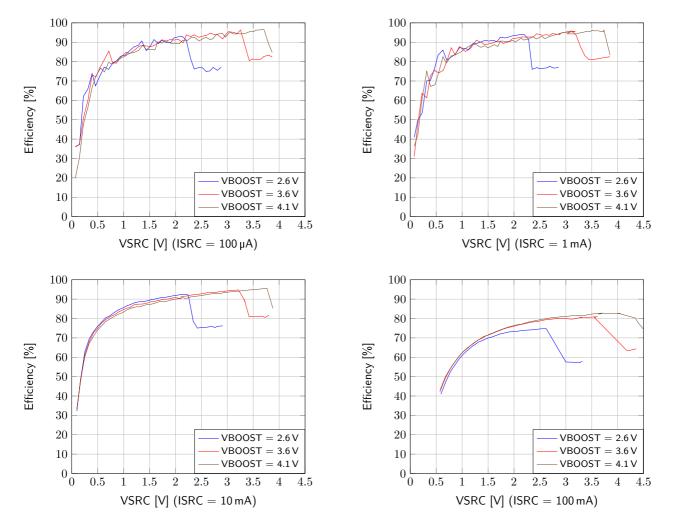


Figure 14: Boost efficiency for Isrc at 100 μ A, 1 mA, 10 mA and 100 mA

10.2 Quiescent current

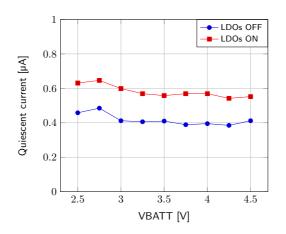


Figure 15: Quiescent current with LDOs on and off



10.3 High-voltage LDO regulation

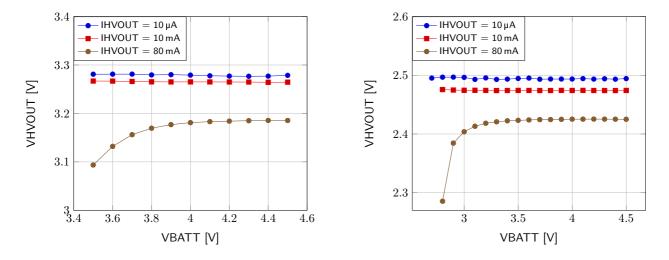


Figure 16: HVOUT at 3.3 V and 2.5 V



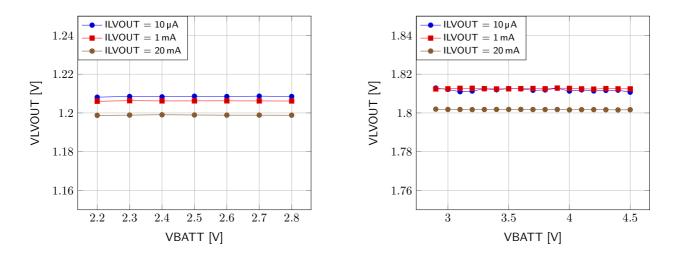


Figure 17: LVOUT at 1.2 V and 1.8 V



10.5 High-voltage LDO efficiency

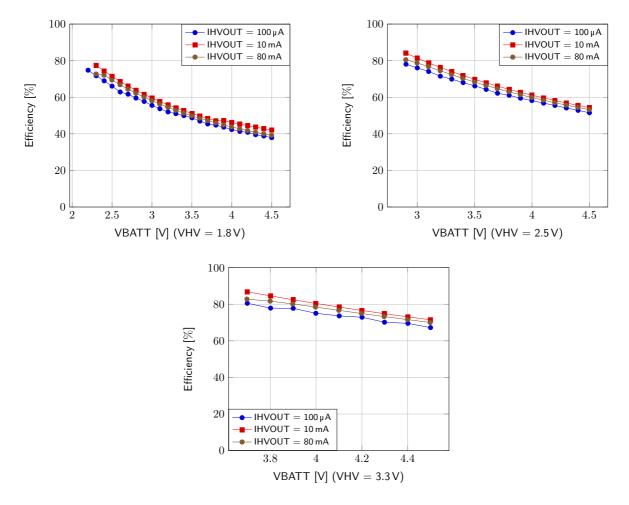


Figure 18: HVOUT efficiency at 1.8 V, 2.5 V and 3.3 V

The theoretical efficiency of a LDO can be simply calculated as $\frac{Vout}{Vin}$ if quiescent current can be neglected with regards to the output current. In the case of the high-voltage LDO, the theoretical efficiency is equal to $\frac{Vhv}{Vbatt}$.

10.6 Low-voltage LDO efficiency

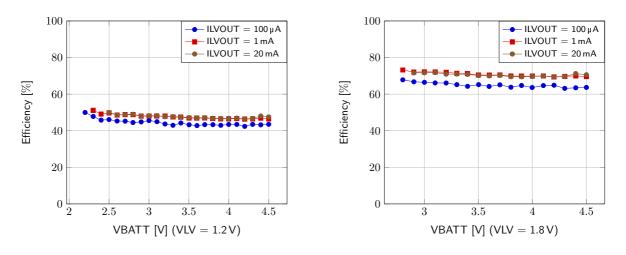


Figure 19: Efficiency of BUCK cascaded with LVOUT at 1.2 V and 1.8 V

The theoretical efficiency of the low-voltage LDO is equal to $\frac{V_{Iv}}{V_{buck}}$. Starting from the battery, the efficiency of the buck converter has to be taken into account (see Figure 4). The efficiency between Vbatt and VIv is therefore equal to η_{buck} .



10.7 RF path efficiency

To be able to harvest efficiently from an RF source with the AEM30940, a matching network and a RF rectifier are necessary. As a reference design, e-peas proposes a low-power and high-power version of the required matching network and rectifier. The low-power reference design offers better efficiency at input power lower than -5 dBm. The high-power reference design offers better efficiency for input power above -5 dBm. Actual designs are proposed for 2 frequency bands: 863-868 MHz and 915-921MHz.

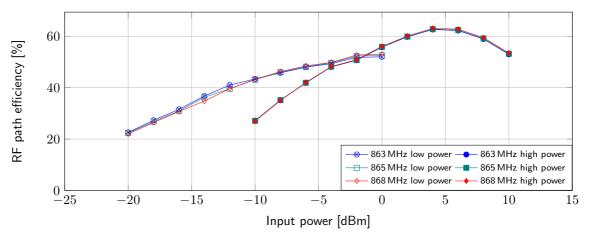


Figure 20: Efficiency for 863-868 MHz band

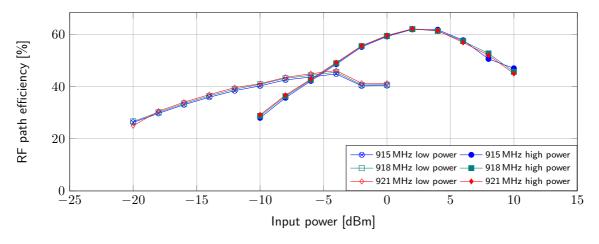


Figure 21: Efficiency for 915-921 MHz band

The RF path efficiency is defined as the ratio between the power available at the output of the rectifier (SRC) and the power at the input of the matching network (50 Ω single input SMA).



10.8 Overall efficiency

As a reminder, the low-power reference design is optimized for input power lower than -5 dBm at the receiver antenna. The high-power reference design is optimized for input power above -5 dBm at the receiver antenna. The overall efficiency is defined as the ratio between the power available at the output of the internal boost converter and the power at the input of the matching network (50Ω single input SMA).

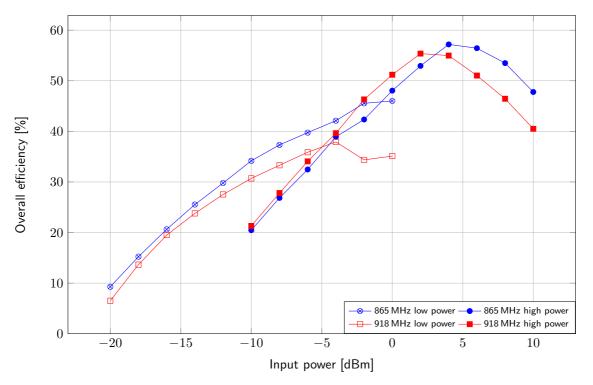


Figure 22: Overall efficiency (RF path and boost converter) with VBOOST = 3.5 V



11 Schematic

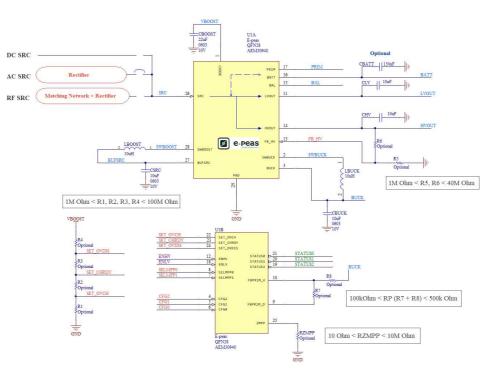


Figure 23: Schematic example

Designator	Description	Quantity	Manufacturer	Part Number
CBOOST	Ceramic Cap 22 μ F, 10 V, 20 %, X5R 0603	1	Murata	GRM188R61A226ME15D
CBUCK	Ceramic Cap 10 μ F, 10 V, 20 %, X5R	1	TDK	C1608X5R1A106M080AC
CHV	Ceramic Cap 10 μ F, 10 V, 20 %, X5R	1	TDK	C1608X5R1A106M080AC
CLV	Ceramic Cap 10 μ F, 10 V, 20 %, X5R	1	TDK	C1608X5R1A106M080AC
CSRC	Ceramic Cap 10 μ F, 10 V, 20 %, X5R	1	TDK	C1608X5R1A106M080AC
LBOOST	Power Inductor 10 μ H - 0,54 A - LPD5030V	1	Coilcraft	LPD5030V-103MR
	Power Inductor 10 μ H - 0,55 A - LPS4012	1	Würth	744 040 321 00
LBUCK	Power Inductor 10 μ H - 0,25 A	1	TDK	MLZ1608M100WT
U1	AEM30940 - Symbol QFN28	1		order at sales@e-peas.com
				or Where to buy

Table 10: BOM example for AEM30940 and its required passive components





12 Layout

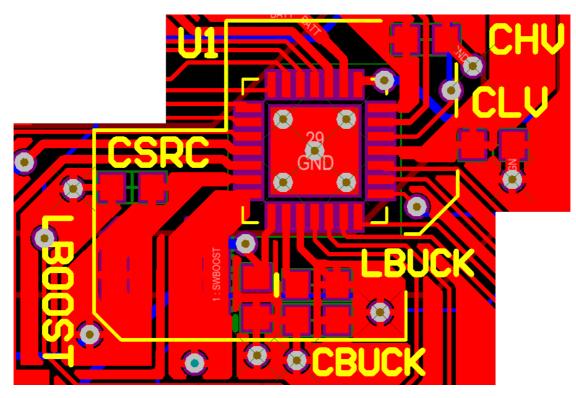


Figure 24: Layout example for the AEM30940 and its passive components

Note: Schematic, symbol and footprint for the e-peas component can be ordered by contacting the e-peas support: support@e-peas.com



13 Package Information

13.1 Plastic quad flatpack no-lead (QFN28 5x5mm)

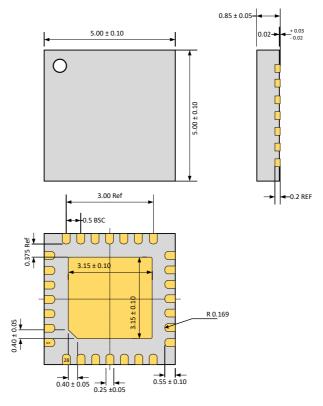


Figure 25: QFN28 5x5mm

13.2 Board layout

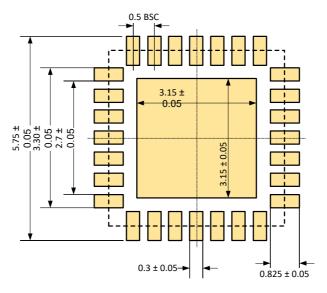


Figure 26: Board layout





Revision history

Revision	Date	Description		
1.0	July, 2018	Creation of the document.		
1.2	June, 2019	 p21, 22 → Updated efficiencies measurements; p5 → ESD specifications; p3 → HVOUT voltage on Figure 1 4.2V → 4.1V; p1, 3, 7, 8 → AC source instead of Power receiving antenna for front page Figure , Figure 1, Figure 3 and Figure 4. 		